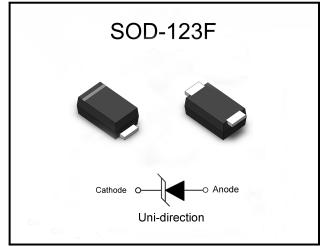


## Transient Voltage Suppressor

#### **Features**

- Peak power disspation 200W@10 x 1000 us Pluse
- · Low incremental surge resistance
- · Excellent clamping capability
- · Excellent clamping capability
- · Fast response time
- · Halogen free and RoHS compliant
- · Lead-free finish

## Package



#### **Mechanical Characteristics**

- Package: SOD-123FL plastic package.
- · Lead Finish: Matte Tin
- Case Material: Epoxy Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020

#### **Applications**

- Telecom
- Computer
- · Industrial electronic
- · Consumer electronic
- Automotive electronic

#### **Making Code**



#### **Summary of Packing Options**

| Order code | Package   | Base qty | Delivery mode |
|------------|-----------|----------|---------------|
| SMF3.3A    | SOD-123FL | 3000     | Tape and reel |

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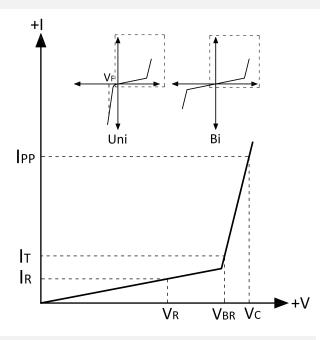




## Transient Voltage Suppressor

#### **Electrical Parameters**

| Parameter       | Definition   |
|-----------------|--|
| СЈ              | Junction Capacitance - typical capacitance         |
|                 | measured with 0V or V <sub>R</sub> bias            |
| 1               | Peak Pulse Current - maximum rated peak            |
| I <sub>PP</sub> | impulse current                                    |
| V <sub>C</sub>  | Clamping Voltage - Peak voltage measured           |
|                 | across the suppressor at a specified lppm          |
| $V_{BR}$        | Breakdown Voltage - Maximum voltage that flows     |
|                 | though the TVS at a specified test current $(I_T)$ |
| I_              | Leakage Current - maximum peak off-state           |
| I <sub>R</sub>  | current measured at V <sub>R</sub>                 |
| V <sub>R</sub>  | Peak Off-state Voltage - maximum voltage           |
|                 | that can be applied while maintaining off state    |



#### Absolute Maximum Ratings $(T_A = +25^{\circ}C, \text{ nless otherwise noted})$

| Parameter  |                  | Value      | Units |
|--|------------------|------------|-------|
| Peak Pulse Power Dissipation on 10/1000 us Waveform(Note1,2,FIG.1) |                  | 200        | W     |
| Power Dissipation on Infinite Heat Sink at T <sub>L</sub> =50°C    |                  | 1          | W     |
| Peak Pulse Current of on 10/1000 us Waveform(Note1,FIG.3)          | I <sub>PPM</sub> | See Table  | А     |
| Peak Forward Surge Current,8.3ms Single Half Sine-Wave(Note2.3)    | I <sub>FSM</sub> | 20         | А     |
| Operating Junction Temperature Range                               | TJ               | -55 to 150 | °C    |
| Storage Temperature Range  | TJ               | -55 to 150 | °C    |

#### Notes:

- (1) Non-repetitive current pulse, per Fig.3 and derated above TA=25°C per Fig.2.
- (2) Mounted on 5.0x5.0mm<sup>2</sup> (0.03mm thick) Copper Pads to each terminal.
- (3) Measured on 8.3ms single half sine-wave, or equivalent square wave, for Unidirectional device only.

#### Absolute Maximum Ratings (T<sub>A</sub>=+25°C, unless otherwise noted)

| Part<br>Number | Reverse<br>Stand-Off<br>Votage | Breakdown<br>Voltage<br>V <sub>BR</sub> @I <sub>T</sub> |         | Test<br>Current<br>I <sub>T</sub> | Maximum<br>Clamping<br>Voltage<br>V <sub>C</sub> @ I <sub>pp</sub> | Maximum<br>Peak Pulse<br>Current<br>I <sub>pp</sub> | Maximun<br>Reverse<br>Leakage<br>I <sub>R</sub> @V <sub>R</sub> |
|----------------|--------------------------------|---|---------|-----------------------------------|--|---|---|
| (Uni)          | (V)                            | Min.(V)   | Max.(V) | (mA)                              | (V)  | (A)   | (uA)  |
| SMF3.3A        | 3.3                            | 5.0   | 5.8     | 10                                | 7.6  | 26.3  | 50  |

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## Transient Voltage Suppressor

#### **Ratings and Characteristic Curves**

Figure 1: Peak Pulse Power Rating

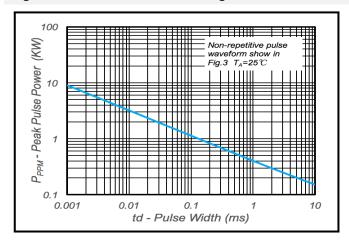


Figure 2: Pulse Derating Cure

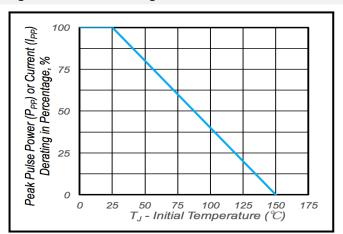
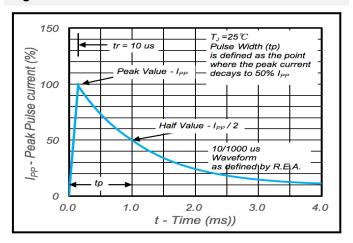
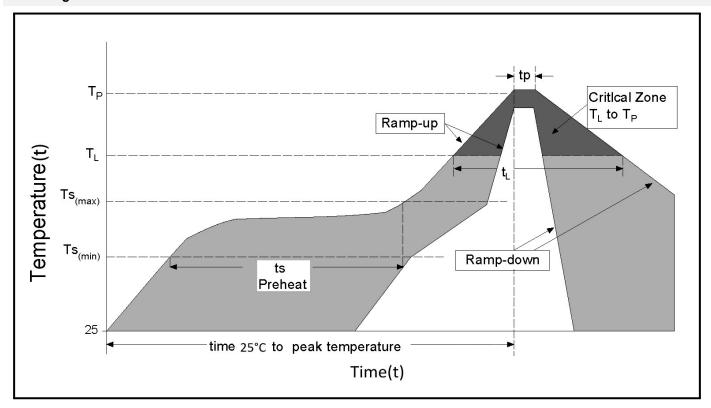


Figure 3: Pulse Waveform



## Transient Voltage Suppressor

#### **Soldering Parameters**



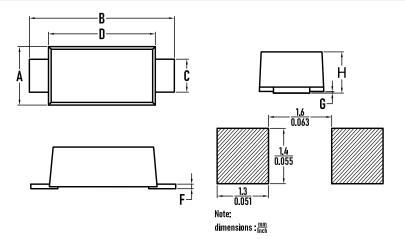
| Reflow 0   | Lead-free assembly   |                |  |
|--|--|----------------|--|
|  | - Temperature Min (T <sub>S</sub> (min))                       | 150°C          |  |
| Pre Heat   | - Temperature Max (T <sub>S</sub> (max))                       | 200°C          |  |
|  | - Time (min to max) (t <sub>S</sub> )                          | 60 - 180 secs  |  |
| Average ramp up rate (Lic                                    | Average ramp up rate (Liquidus Temp (T <sub>L</sub> ) to peak) |                |  |
| $T_{S}(max)$ to $T_{L}$ -                                    | T <sub>S</sub> (max) to T <sub>L</sub> - Ramp-up Rate          |                |  |
| Reflow   | - Temperature (T <sub>L</sub> ) (Liquidus)                     | 217°C          |  |
| Kellow   | - Time (t <sub>L</sub> )                                       | 60 -150 secs   |  |
| Peak Temp  | 260 <sup>+0/-5°C</sup>   |                |  |
| Time within 5°C of actual peak Temperature (t <sub>p</sub> ) |  | 6°C/second max |  |
| Ramp-down Rate   |  | 6°C/second max |  |
| Time 25°C to peak Temperature (t)                            |  | 8 minutes Max. |  |
| Do not exceed  |  | 260°C          |  |





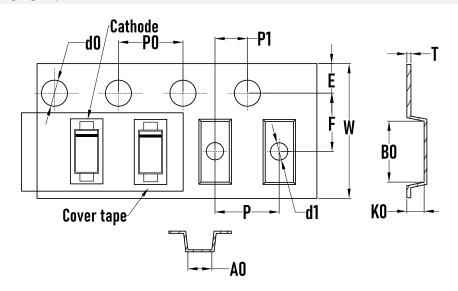
#### **ESD Protection Diode**

### Package Mechanical Data - SOD-123FL



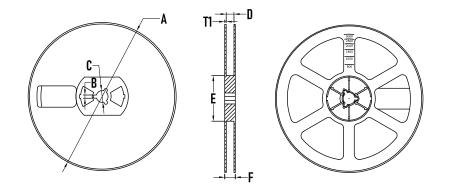
| SYMBOL   | MILLIMETER |      |      |  |
|----------|------------|------|------|--|
| STIVIBOL | MIN.       | Тур. | MAX. |  |
| Α        | 1.60       | 1.80 | 2.00 |  |
| В        | 3.40       | 3.60 | 3.80 |  |
| С        | 0.90       | 1.00 | 1.10 |  |
| D        | 2.50       | 2.70 | 2.90 |  |
| F        | 0.10       | 0.15 | 0.20 |  |
| G        | 0.00       | _    | 0.02 |  |
| Н        | 1.00       | 1.10 | 1.20 |  |

#### Packaging Tape - SOD-123FL



| SYMBOL | MILLIMETER |
|--------|------------|
| A0     | 2.10±0.1   |
| В0     | 4.0 ±0.1   |
| d0     | 1.5±0.1    |
| d1     | 1.0±0.1    |
| Е      | 1.75±0.1   |
| F      | 3.50±0.1   |
| K0     | 1.25±0.1   |
| Р      | 4.00±0.1   |
| P0     | 4.00±0.1   |
| P1     | 2.00±0.1   |
| W      | 8.00±0.1   |
| Т      | 0.2±0.02   |

#### **Packaging Reel**



| SYMBOL   | MILLIMETER |
|----------|------------|
| А        | 177.8±0.2  |
| В        | 2.7±0.2    |
| С        | 13.5±0.2   |
| D        | 9.6±0.3    |
| Е        | 54.5±0.2   |
| F        | 12.3±0.3   |
| T1       | 1.0±0.2    |
| Quantity | 3000PCS    |

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